Made in USSR

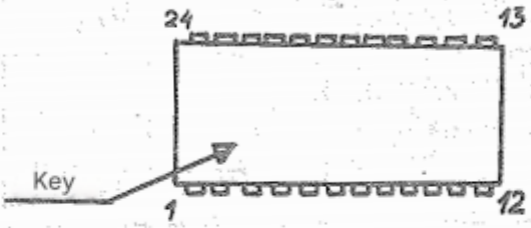
LABEL

MICROCIRCUIT TYPE K573RF2

Read-only memory device with ultraviolet erasure and electrical recording of information, with a long storage period of information with the supply voltage on or off.

Number of information words - 2048, number of digits in an information word - 8.

Pinout diagram



The designation of the terminals is shown conditionally.

The shape of the key is not regulated.

Weight no more than 5 g.

MAIN ELECTRICAL PARAMETERS UNDER NORMAL CLIMATIC CONDITIONS

Low-level voltage of the output information signal, V	no more than 0.4
High-level voltage of the output information signal, V	no less than 2.4
Information storage time with the supply voltage on, V	no less than 25000
Information storage time with the supply voltage off, h	no less than 100000
Address sampling time, m.s	no more than 0.45
Number of reprogramming cycles, cycle	no less than 100

MAXIMUM PERMISSIBLE AND LIMIT OPERATING MODES

Parameter name, mode, unit of measurement	Letter-new designation reading	Norm			
		maximum permissible mode		limit mode πάτωμ	
		no less	more	no less	no more
Low level voltage of input signals, V	UDILUA$_{AT}$, UCEL UOEL	–	0.4	-0.3	0.8
High level voltage U of input signals,	I $_{OEH}$, U_{DIH} U_{AH}, U_{CEH}	2.4	–	2.0	6.0
Supply voltage, I	U_{CC}	4.75	5.25	-0.3	6.0
High level write signal voltage, U	U_{WRH}	23.5	25.5	-0.3	26.0
Low level write signal voltage, I	U_{WRL}	4.75	5.25	-0.3	6.0
Storage temperature of 3 microcircuits, K	T	228	349	2I3	398

Notes:

I. Voltage values are given relative to pin 12.

2. After storing microcircuits at maximum temperature 398K information must be erased and rewritten.

ELECTRICAL MODES DURING OPERATION

Functional state of the microcircuit	Functional purpose and pin number				
	"Address input" (8-1,19,22,23)	"Appeal enable signal input" (18)	"Output enable signal input (20)	"Read-write signal input" (21)	"Exit-entrance" (9-11, 13-17)
Reading information	U_{AL}, U_{AH}	U_{CEL}	U_{OEL}	U_{WRL}	UDOLPH 10 2.1m UDOH, at I OH -0.4mA
Failure to select a chip	Arbitrarily	U_{CEL}	U_{OEL}	U_{WRL}	State "Off"
Reducing power consumption	Arbitrarily	U_{CEL}	Arbitrarily	U_{WRL}	State "Off"
Programming (recording)	U_{AL}, U_{AH}	Impulse U CEH	U_{OEH}	U_{WRH}	U_{DIL} , U_{DIH}
Control after programming	U_{AL}, U_{AH}	U_{CEL}	U_{OEL}	U_{WRH}	U_{DOL} при $I_{OL} \geq 2,1$ mA UDOH dri Gon-0,4mA
Disable programming (writing)	Arbitrarily	U_{CEL}	U_{OEH}	U_{WRH}	State "Off"
Erasing information	Irradiation of the microcircuit crystal with UV radiation l≤ 400 nm property radiation at A = 253.7 nm • Temperature no more than 343 K.			with energy housing at	pre- this

Note: UAL-UCEL=UOEL=(0-0.4)V; UAH-UCEH-UOEH=(2.4-5.25)V; UCC=UWRL=5 V±5%;UWRH=(23.5-25.5)V

Conclusion 24 - UCC.